



DMN6040SVTQ

60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D T _A = +25°C
60V	$44m\Omega$ @ $V_{GS} = 10V$	5.0A
607	60mΩ @ V _{GS} = 4.5V	4.3A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

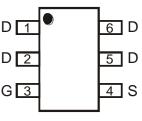
- DC-DC Converters
- Power Management Functions
- Backlighting

Mechanical Data

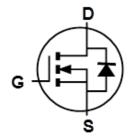
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.013 grams (Approximate)







Top View Pin Configuration



Equivalent Circuit

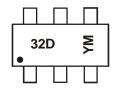
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN6040SVTQ-7	TSOT26	3,000/Tape & Reel
DMN6040SVTQ-13	TSOT26	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



32D = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

Date Code Key

Year	2010		2017	2018	3 20°	19 2	020	2021	2022	2023	2024	2025
Code	Х		Е	F	G	;	Н	ı	J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

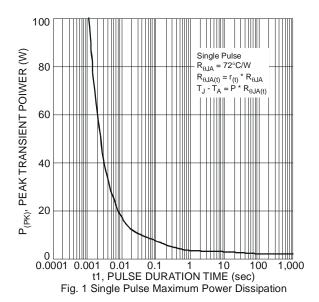
Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	60	V		
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V 40V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	5.0 4.0	А
Continuous Drain Current (Note 7) V _{GS} = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	6.3 5.0	А
Continuous Drain Compant (Note 7) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	4.3 3.4	А
Continuous Drain Current (Note 7) V _{GS} = 5V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	5.4 4.3	А
Maximum Body Diode Forward Current (Note 7)	Is	2.1	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	30	Α		
Avalanche Current (Note 8) L = 0.1mH	I _{AR}	14.2	Α		
Avalanche Energy (Note 8) L = 0.1mH	E _{AR}	10	mJ		

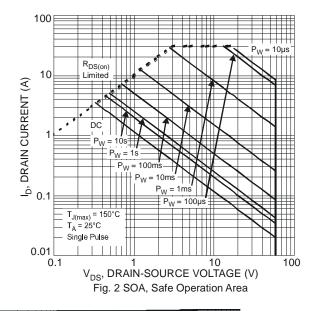
Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

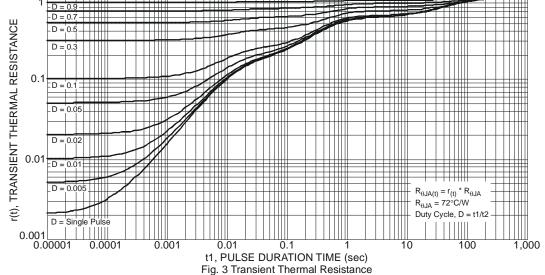
Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 6)	$T_A = +25$ °C	C	1.2	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	0.75		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	C	106	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	69	°C/W	
Total Power Dissipation (Note 7)	$T_A = +25^{\circ}C$	C	1.8	W	
Total Power Dissipation (Note 1)	$T_A = +70^{\circ}C$	P_{D}	1.1		
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	0	68	°C/W	
Thermal Resistance, Junction to Ambient (Note 7)	t<10s	$R_{\theta JA}$	44	°C/W	
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	20	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 8. IAR and EAR rating are based on low frequency and duty cycles to keep $T_J = +25$ °C.











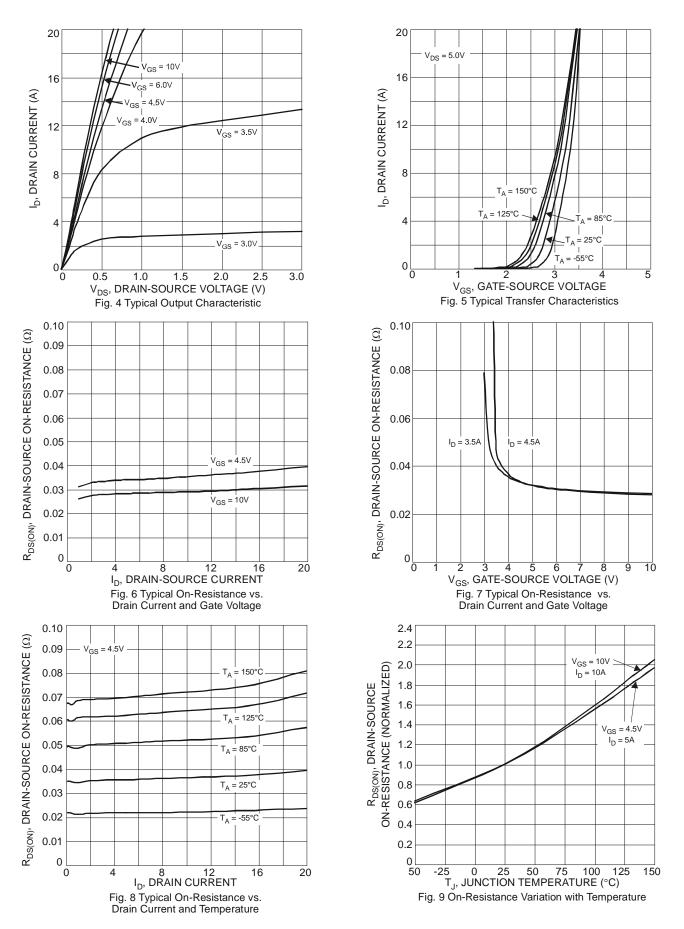
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	100	nA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1		3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			30	44	mΩ	$V_{GS} = 10V, I_D = 4.3A$	
Static Diain-Source Off-Resistance	R _{DS(ON)}		35	60	11152	$V_{GS} = 4.5V, I_D = 4A$	
Forward Transfer Admittance	Y _{FS}		4.5	_	S	$V_{DS} = 10V, I_D = 4.3A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	CISS		1,287	_		$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss		57	_	pF		
Reverse Transfer Capacitance	C _{RSS}		44	_		1 = 1.0IVII IZ	
Gate Resistance	Rg	_	1.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_G	_	22.4				
Total Gate Charge (V _{GS} = 4.5V)	Q_G	_	10.4	_	nC	V 20V L 42A	
Gate-Source Charge	Q _{GS}	_	4.9	_	IIC	$V_{DS} = 30V, I_{D} = 4.3A$	
Gate-Drain Charge	Q_{GD}	_	3.0	_			
Turn-On Delay Time	t _{D(ON)}	_	6.6				
Turn-On Rise Time	t _R	_	8.1	_		$V_{GS} = 10V$, $V_{DD} = 30V$, $R_{G} = 6\Omega$,	
Turn-Off Delay Time	t _{D(OFF)}	_	20.1		ns	$I_D = 4.3A$	
Turn-Off Fall Time	t _F		4.0				
Body Diode Reverse Recovery Time	t _{RR}	_	18		ns	I _S = 4.3A, dI/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	11.9		nC	I _S = 4.3A, dl/dt = 100A/µs	

Notes:

^{9.} Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.







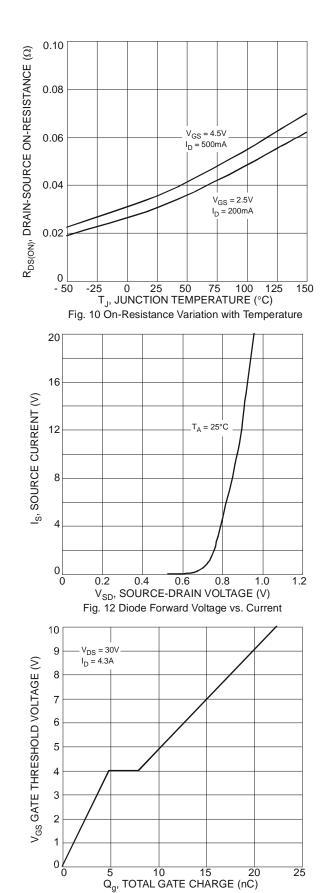


Fig. 14 Gate Charge

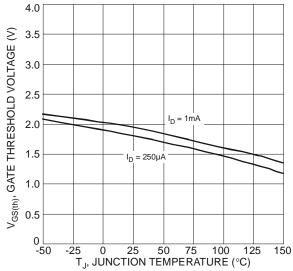
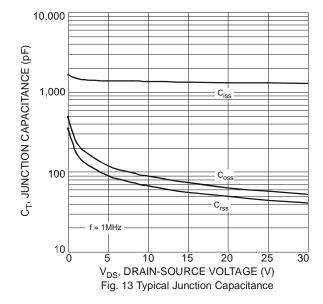


Fig. 11 Gate Threshold Variation vs. Ambient Temperature

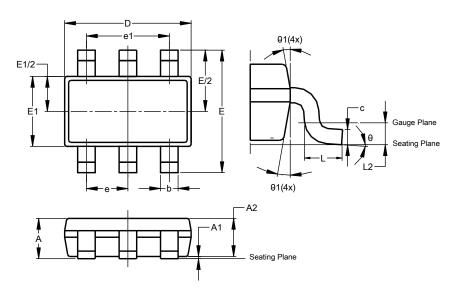




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

TSOT26

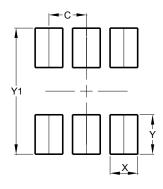


TSOT26							
Dim	Min	Max	Тур				
Α	-	1.00	-				
A 1	0.010	0.100	-				
A2	0.840	0.900	-				
D	2.800	3.000	2.900				
Е	2	.800 BS	С				
E1	1.500	1.700	1.600				
b	0.300	0.450	-				
С	0.120	0.200	-				
е	0.950 BSC						
e1	1	.900 BS	С				
L	0.30	0.50					
L2	0.250 BSC						
θ	0°	8°	4°				
θ1	4°	12°	_				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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